

UHF POWER LDMOS TRANSISTOR

DESCRIPTION:

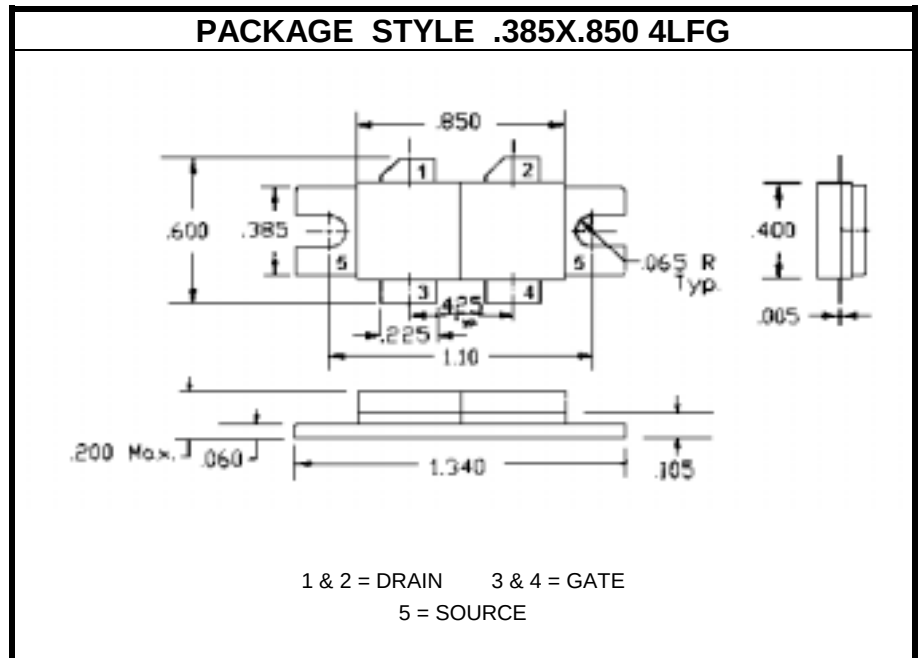
The **ASI BLF861A** is a Silicon N-channel enhancement mode lateral D-MOS push-pull transistor.

FEATURES:

- Internal input-output matching
- **OmniGold™** Metalization System

MAXIMUM RATINGS

I_D	18 A
V_{DS}	65 V
V_{GS}	± 15 V
P_{DISS}	318 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.55 $^\circ\text{C/W}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_D = 1.5$ mA	65			V
I_{DSS}	$V_{DS} = 32$ V $V_{GS} = 0$ V			2.2	μA
I_{DSX}	$V_{DS} = 10$ V $V_{GS} = V_{GSth} + 9$ V	18			A
I_{GSS}	$V_{DS} = 0$ V $V_{GS} = \pm 15$ V			25	nA
$V_{GS(th)}$	$I_D = 150$ mA $V_{DS} = 10$ V	4.0		5.5	V
$R_{DS(on)}$	$I_D = 4.0$ A $V_{GS} = V_{GSth} + 9$ V		160		m Ω
g_{fs}	$I_D = 4.0$ A $V_{DS} = 10$ V		4.0		S
C_{iss} C_{oss} C_{rss}	$V_{DS} = 32$ V $V_{GS} = 0$ V $f = 1.0$ MHz		82 40 6.0		pF
G_p η_D	$V_{DS} = 32$ V $P_{out} = 150$ W $f = 860$ MHz	13.5 50	14.5		dB %